

**Amendments to the Claims**

1. (CURRENTLY AMENDED) A method of forming shaped structures on a device plate ~~(2, 20)~~ comprising applying a photosensitive layer ~~(6, 19)~~ to said plate, and forming the shaped structures on the photosensitive layer in a photolithographic process using a grey-tone photo mask ~~(7, 21)~~ which comprises at least one region of semi-transparent material ~~(8, 16, 18)~~ said material having a degree of transparency which is dependent on the optical band gap of the material.
2. (ORIGINAL) A method according to claim 1 wherein the material regions used in the grey-tone photo mask are hydrogenated silicon-rich silicon nitride  $\text{SiN}_x\text{:H}$  with x less than 1.
3. (CURRENTLY AMENDED) A method according to ~~claim 1 or 2~~ claim 1 wherein, prior to forming of the shaped structures in the liquid crystal display cells, the method further comprises the steps of forming the photo mask ~~(7, 21)~~ including:
  - depositing a layer of said semi-transparent material to form said region of semi-transparent material ~~(16)~~ on a UV-transparent substrate ~~(15)~~;
  - patterning said semi-transparent material;
  - depositing a layer of UV-opaque material ~~(17)~~ onto the substrate; and
  - patterning said layer of UV-opaque material.
4. (CURRENTLY AMENDED) A method according to claim 3, including:
  - depositing a layer of a second semi-transparent material ~~(18)~~ having a different degree of transparency to the first material, where the degree of transparency is dependent on the optical band gap of the material, to form a second region of semi-transparent material ~~(18)~~ on said UVtransparent substrate; and
  - patterning said second semi-transparent material.
5. (CURRENTLY AMENDED) A method according to claim 4 including patterning once again said layer of UV-opaque material ~~(17)~~.

6. (CURRENTLY AMENDED) A method according to ~~claim 3, 4 or 5~~claim 3, wherein the UV-opaque material ~~(17)~~ is Cr.

7. (CURRENTLY AMENDED) A method according to ~~any preceding claim~~claim 1 wherein said photo mask is used in said photolithographic process so as to produce an irregular surface topography for a diffusely reflective pixel electrode of a liquid crystal display.

8. (CURRENTLY AMENDED) A method according to claim 7 wherein said surface topography for said diffusely reflective pixel electrode of the liquid crystal display has multiple levels of thickness.

9. (CURRENTLY AMENDED) A method according to ~~any preceding claim~~claim 1 including forming an a AMLCD including the device plate.

10. (CURRENTLY AMENDED) A liquid crystal display device fabricated by a method as claimed in ~~any preceding claim~~claim 1.

11. (ORIGINAL) A mask configured for use in a method as claimed in claim 1.